General Description

These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

BVDSS	RDSON	ID
100V	6.2mΩ	90A

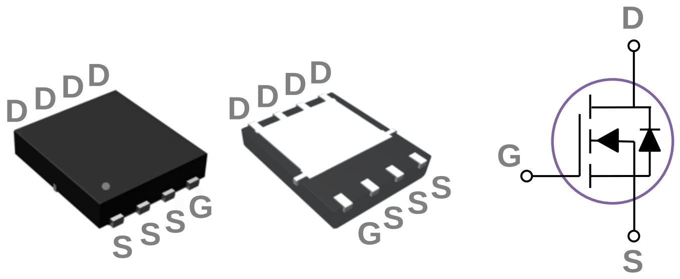
Features

- *100V,90A, RDS(ON) =6.2mΩ@VGS = 10V*
- *Improved dv/dt capability*
- *Fast switching*
- *100% EAS Guaranteed*
- *Green Device Available*

Applications

- *Networking*
- *Load Switch*
- *LED applications*
- *Quick Charger*

PPAK5X6 Pin Configuration



Absolute Maximum Ratings T_C=25℃ unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Drain Current – Continuous (T_C=25℃)	90	A
	Drain Current – Continuous (T_C=100℃)	57	A
I_{DM}	Drain Current – Pulsed[1]	360	A
EAS	Single Pulse Avalanche Energy[2]	205	mJ
IAS	Single Pulse Avalanche Current[2]	64	A
P_D	Power Dissipation (T_C=25℃)	134	W
	Power Dissipation – Derate above 25℃	1.08	W/℃
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	62	℃/W
$R_{\theta JC}$	Thermal Resistance Junction to Case	---	0.93	℃/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250μA	100	---	---	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=80V , V_{GS}=0V , T_J=25℃	---	---	1	μA
		V_{DS}=80V , V_{GS}=0V , T_J=85℃	---	---	10	μA
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA

On Characteristics

$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V , I_D=15A	---	5.2	6.2	mΩ
		V_{GS}=4.5V , I_D=8A	---	6.8	8.8	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250μA	1.2	1.6	2.5	V
gfs	Forward Transconductance	V_{DS}=10V , I_D=3A	---	14	---	S

Dynamic and switching Characteristics

Q_g	Total Gate Charge^{3,4}	V_{DS}=50V , V_{GS}=10V , I_D=45A	---	37	55	nC
Q_{gs}	Gate-Source Charge^{3,4}		---	5.3	8	
Q_{gd}	Gate-Drain Charge^{3,4}		---	8.7	13	
$T_{d(on)}$	Turn-On Delay Time^{3,4}	V_{DD}=50V , V_{GS}=10V , R_G=6Ω I_D=45A	---	15	23	ns
T_r	Rise Time^{3,4}		---	28	42	
$T_{d(off)}$	Turn-Off Delay Time^{3,4}		---	45	68	
T_f	Fall Time^{3,4}		---	32	48	
C_{iss}	Input Capacitance	V_{DS}=50V , V_{GS}=0V , F=1MHz	---	2420	3620	pF
C_{oss}	Output Capacitance		---	320	480	
C_{rss}	Reverse Transfer Capacitance		---	10	15	
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, F=1MHz	---	1.5	---	Ω

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	V_G=V_D=0V , Force Current	---	---	90	A
I_{SM}	Pulsed Source Current		---	---	180	A
V_{SD}	Diode Forward Voltage	V_{GS}=0V , I_S=1A , T_J=25℃	---	---	1	V
t_{rr}	Reverse Recovery Time	V_R=100V, I_R=10A di/dt=100A/μs , T_J=25℃	---	220	---	ns
Q_{rr}	Reverse Recovery Charge		---	435	---	nC

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. V_{DD}=50V,V_{GS}=10V,L=0.1mH,I_{AS}=64A.,R_G=25Ω,Starting T_J=25℃.
3. The data tested by pulsed , pulse width ≦ 300μs , duty cycle ≦ 2%.
4. Essentially independent of operating temperature.

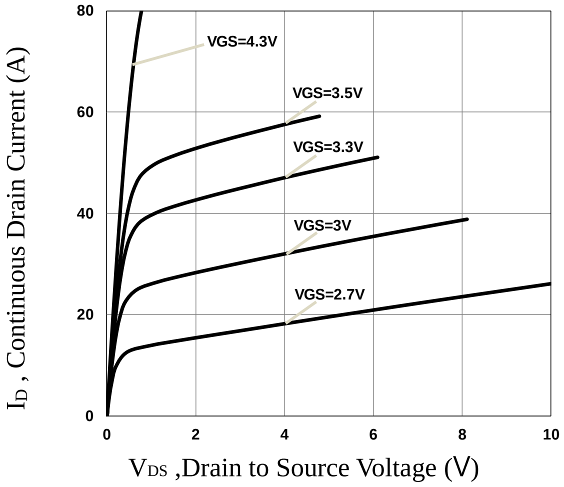


Fig.1 Typical Output Characteristics

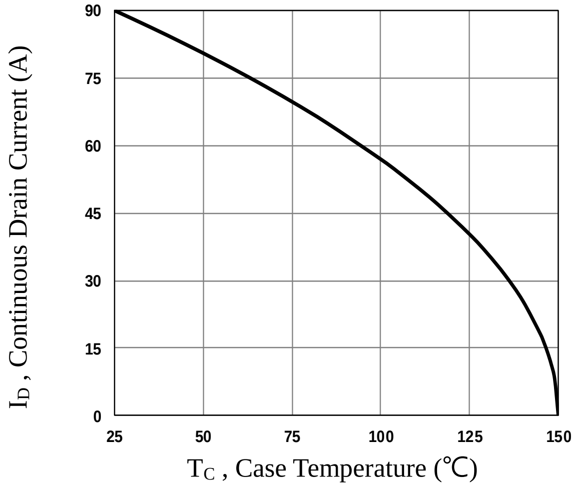


Fig.2 Continuous Drain Current vs. T$_C$

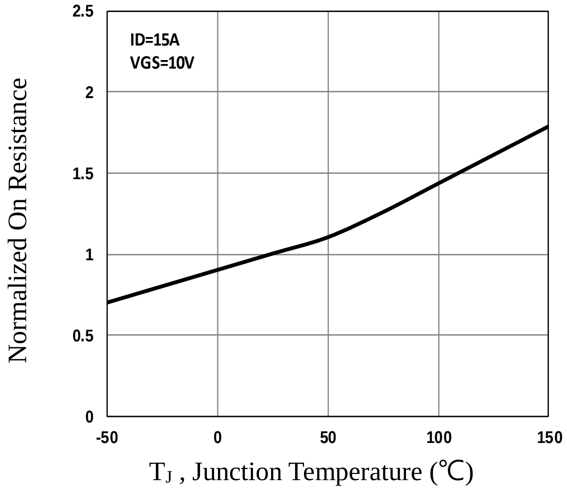


Fig.3 Normalized RDSON vs. T$_J$

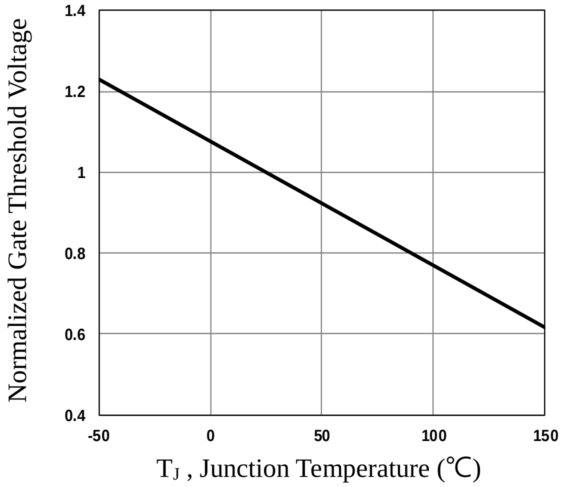


Fig.4 Normalized V$_{th}$ vs. T$_J$

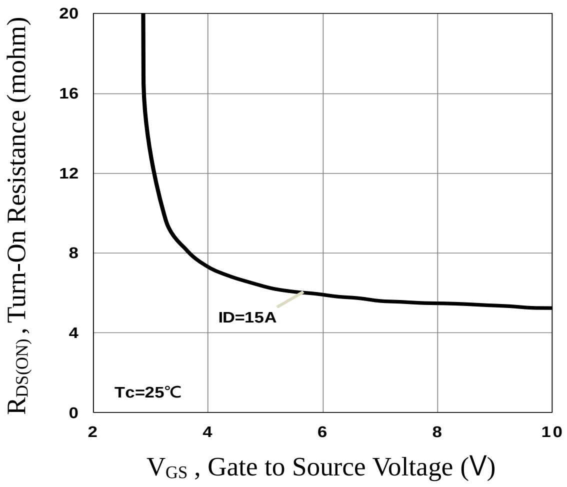


Fig.5 Turn-On Resistance vs. V$_{GS}$

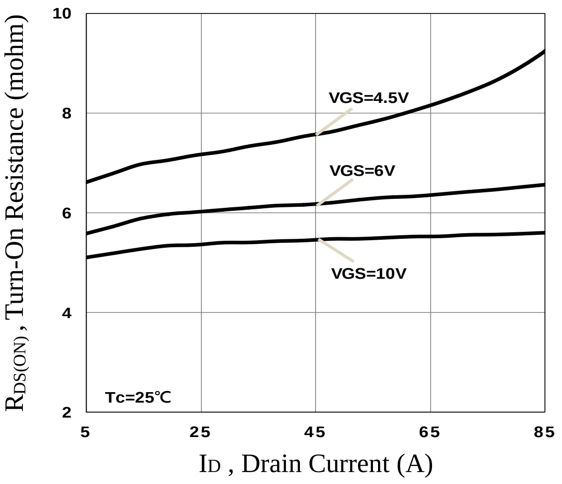


Fig.6 Turn-On Resistance vs. I$_D$

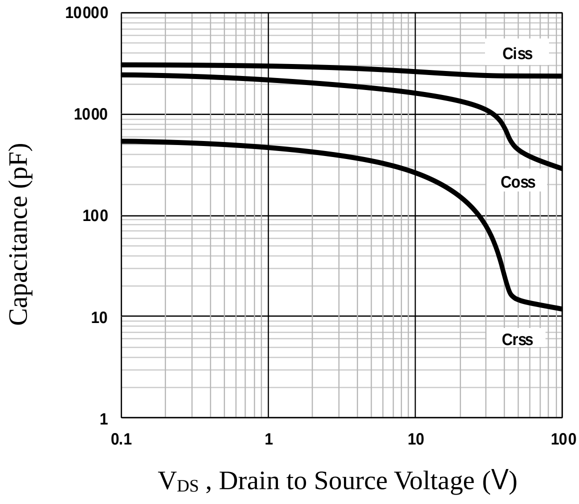


Fig.7 Capacitance Characteristics

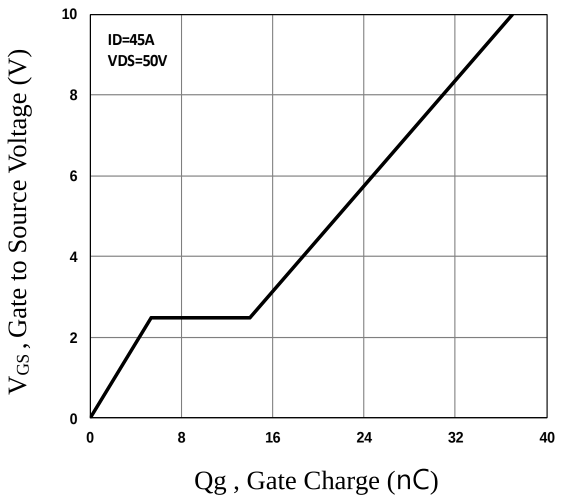


Fig.8 Gate Charge Characteristics

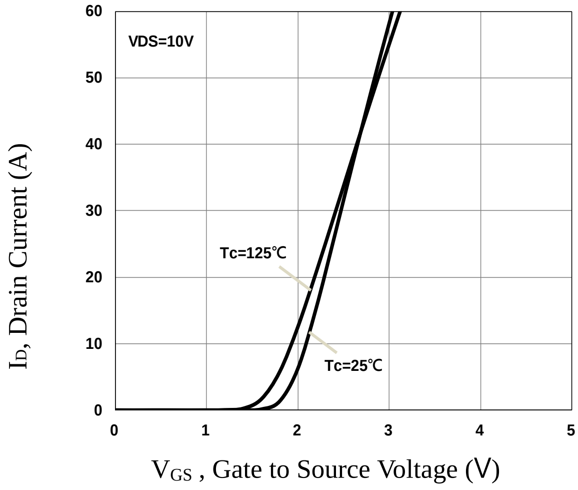


Fig.9 Transfer Characteristics

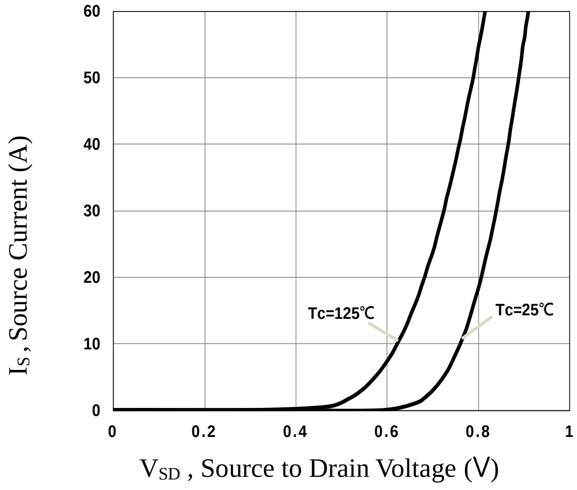


Fig.10 Source Current vs. V_{SD}

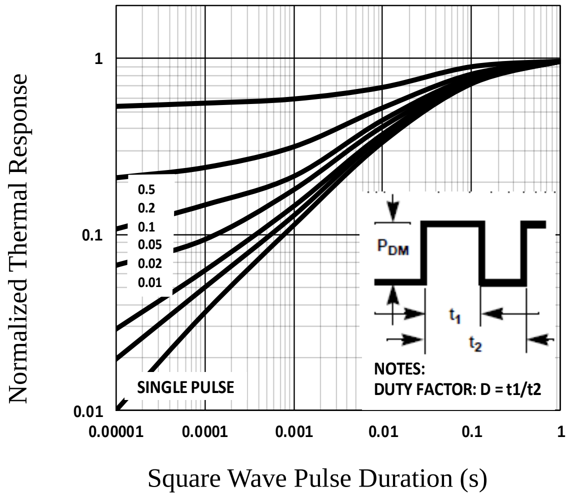


Fig.11 Normalized Transient

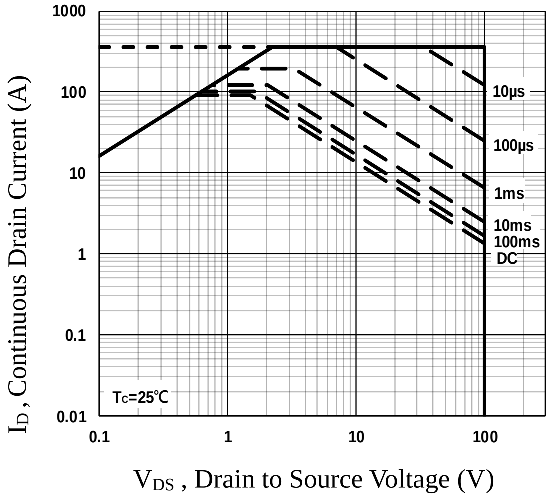
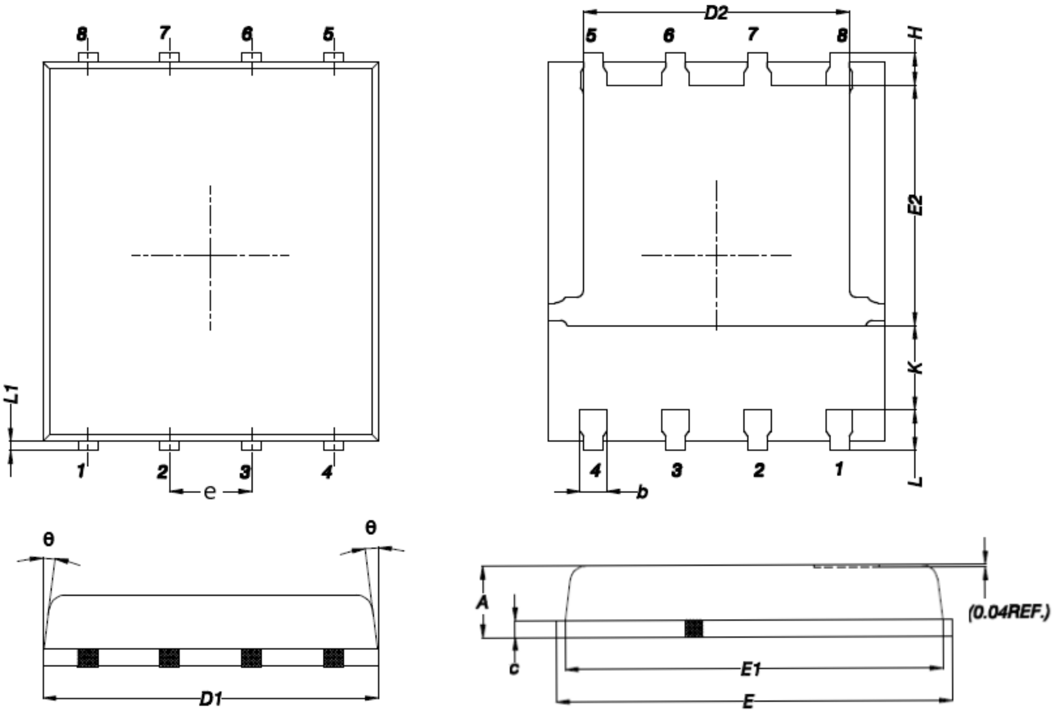


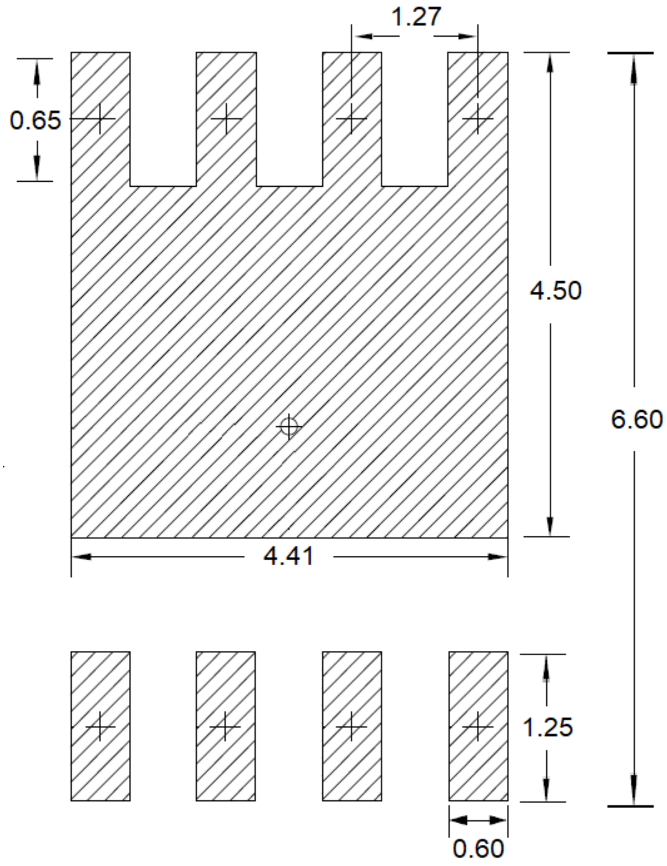
Fig.12 Maximum Safe Operation Area

PPAK5x6 PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MAX	MIN	MAX	MIN
A	1.200	0.850	0.047	0.031
b	0.510	0.300	0.020	0.012
C	0.300	0.200	0.012	0.008
D1	5.400	4.800	0.212	0.189
D2	4.310	3.610	0.170	0.142
E	6.300	5.850	0.248	0.230
E1	5.960	5.450	0.235	0.215
E2	3.920	3.300	0.154	0.130
e	1.27BSC		0.05BSC	
H	0.650	0.380	0.026	0.015
K	---	1.100	---	0.043
L	0.710	0.380	0.028	0.015
L1	0.250	0.050	0.009	0.002
θ	12°	0°	12°	0°

PPAK5X6 RECOMMENDED LAND PATTERN



unit : mm